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WHAT IS CLAIMED IS:

- 1. A semiconductor integrated circuit comprising:

 a pad to which an input signal is externally input;

 an input stage circuit connected to said pad; and

 a buffer circuit having an input terminal connected

 to said pad and an output terminal connected to

 charge or discharge a parasitic capacitance

 between said pad and a semiconductor substrate.
- 2. The semiconductor integrated dircuit defined in Claim 1, further comprising an island region containing impurities of a second conductivity type formed on the upper surface of said semiconductor substrate, and a pad formed on said island region via an oxide film; wherein said semiconductor substrate contains impurities of a first conductivity type; and wherein said output terminal of said buffer circuit is connected to said island region.
- 3. The semiconductor integrated circuit defined in Claim 2, wherein said island region is surrounded with an isolation region containing impurities of a first conductivity type.
- 4. The semiconductor integrated circuit defined in Claim 2, wherein said first conductivity type is a P type and said second conductivity type is an N type.
- 5. The semiconductor integrated circuit defined in Claim 1, wherein said output terminal of said buffer circuit is

connected with said island region by way of a metal conductor.

- 6. The semiconductor integrated circuit defined in Claim 1, wherein the input impedance of said input stage circuit is set to a high value.
- 7. The semiconductor integrated circuit defined in Claim 6, wherein said input stage gircuit comprises an amplifier.
- 8. The semiconductor integrated circuit defined in Claim 6, wherein said input stage circuit comprises a field effect transistor integrated on said semiconductor substrate, said field effect transistor having a gate connected to said pad.
- 9. The semiconductor integrated circuit defined in Claim 8, wherein said field effect transistor has a drain connected to a power source, and a source connected to the ground via a constant current source, for producing an output signal.

10. A semiconductor integrated circuit comprising:

- a pad to which an input signal is externally input;
- a source follower circuit including a transistor
 having a gate connected to said pad and a source
 for producing an output signal;
- whereby said source follower circuit discharges and discharges a parasitic capacitance created between said pad and a semiconductor substrate.

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11. The semiconductor integrated circuit defined in Claim 10, further comprising an island region on the upper surface of said semiconductor substrate containing impurities of a second conductivity type, and a pad formed on said island region via an oxide film; and wherein said semiconductor substrate contains impurities of a first conductivity type; and wherein said output terminal of said source follower circuit is connected to said island region.

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12. The semiconductor integrated circuit defined in Claim 11, wherein said island region is surrounded with an isolation region containing impurities of a first conductivity type.

and a

13. The semiconductor integrated circuit defined in Claim 11, wherein said first conductivity type is a P type and said second conductivity type is an N type.

- 14. The semiconductor integrated circuit defined in Claim 10, wherein said output terminal of said buffer circuit is connected said island region by way of a metal conductor.
- 15. The semiconductor integrated circuit defined in Claim 10, wherein the input impedance of said input stage circuit is set to a high value.

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- The semiconductor integrated circuit defined in Claim 15, wherein said input stage circuit comprises an amplifier.
- 17. The semiconductor integrated circuit defined in Claim 15,

wherein said input stage circuit comprises a field effect transistor integrated on said semiconductor substrate, said field effect transistor having a gate connected to said pad

The semiconductor integrated circuit defined in Claim 17, 18. wherein said field effect transistor has a drain connected to a power source, and a source connected to the ground via a constant current source, for producing an output signal.